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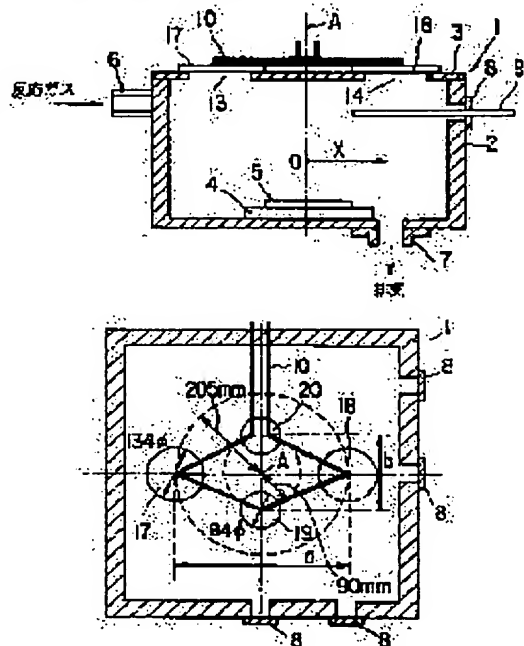
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(54) PLASMA TREATING METHOD AND PLASMA TREATMENT APPARATUS

(57)Abstract:

PROBLEM TO BE SOLVED: To eliminate the need for increasing the area of a dielectric window, even if region generating plasma increases, and allow the window to be thin.

SOLUTION: Four circular holes 13, 14 are formed into a metal top plate 3 attached to a reactor chamber 1, and circular dielectric windows 17-20 are provided in these holes 13, 14 and located on circles which have different diameters with the center at a center axis A of an induced magnetic field by an antenna 10, i.e., at the points of cutting off eddy currents generated by the induced magnetic field on the metal top plate 3 of the reaction chamber 1.



LEGAL STATUS

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